

# HCC/HCF4016B

### **QUAD BILATERAL SWITCH**

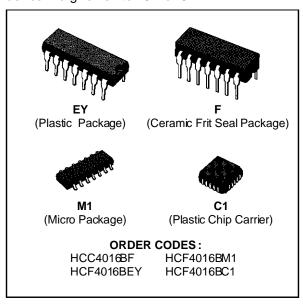
- 20V DIGITAL OR ± 10V PEAK-TO-PEAK SWITCHING
- 280Ω TYPICAL ON RESISTANCE FOR 15V OPERATION
- SWITCH ON RESISTANCE MATCHED TO WITHIN 10Ω TYP. OVER 15V SIGNAL INPUT RANGE
- HIGH ON/OFF OUTPUT-VOLTAGE RATIO : 65dB TYP. @  $f_{is} = 10kHz$ ,  $R_L = 10k\Omega$
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. @  $f_{is}$  = 1KHz,  $V_{is}$  = 5  $V_{pp}$ ,  $V_{DD}$   $V_{SS} \ge 10V$ ,  $R_L$  =  $10k\Omega$
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CURRENT AND HIGH EFFECTIVE OFF RESISTANCE: 100pA TYP. @ VDD VSS = 18V, Tamb = 25°C
- EXTREMELY HIGH CONTROL INPUT IMPED-ANCE (control circuit isolated from signal circuit 10<sup>12</sup>Ω tvp.)
- LOW CROSSTALK BETWEEN SWITCHES : 50dB TYP. @  $f_{is} = 0.9MHz$ ,  $R_L = 1k\Omega$
- MATCHED CONTROL-INPUT TO SIGNAL-OUTPUT CAPACITANCE: REDUCES OUT-PUT SIGNAL TRANSIENTS
- FREQUENCY RESPONSE' SWITCH ON = 40MHz (typ.)
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDECTEN-TATIVE STANDARD N° 13A, "STANDARD SPE-CIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

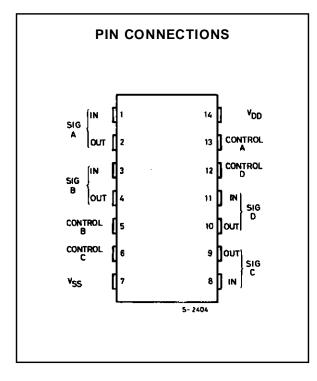
#### **DESCRIPTION**

The **HCC4016B** (extended temperature range) and **HCF4016B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4016B** Series types are quad bilateral switches intended for the transmission or multiplexing

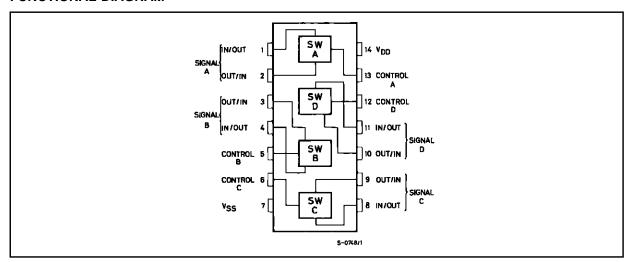
of analog or digital signals. Each of the four independent bilateral switches has a single control signal input which simultaneously biases both the p and n device in a given switch ON or OFF.





June 1989 1/15

#### **FUNCTIONAL DIAGRAM**



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage : <b>HCC</b> Types <b>HCF</b> Types	- 0.5 to + 20 - 0.5 to + 18	V V
$V_{i}$	Input Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
$I_1$	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op}$ = Full Package-temperature Range	200	mW mW
Тор	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

#### **RECOMMENDED OPERATING CONDITIONS**

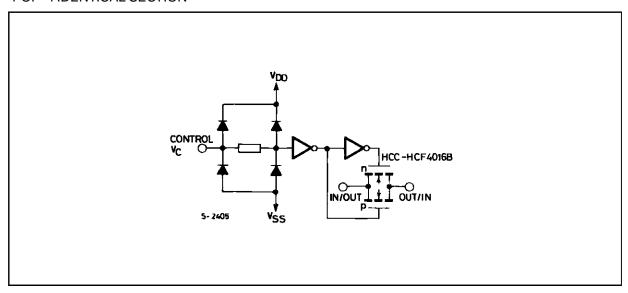
Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
$V_{I}$	Input Voltage	0 to V <sub>DD</sub>	٧
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C



 $<sup>^{\</sup>star}$  All voltage values are referred to  $V_{\text{SS}}$  pin voltage.

#### **SCHEMATIC DIAGRAM**

### 1 OF 4 IDENTICAL SECTION



### STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Test	Condi	tions					Value				
Symbol	Symbol Parameter			V <sub>C</sub> =	$V_{c} = V_{ss}$		DD T <sub>Low</sub> *		25°C			T <sub>High</sub> *		Unit
Cy				$V_{DD}$	(V)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent					5		0.25		0.01	0.25		7.5	
	Device Current (all	HCC Types				10		0.5		0.01	0.5		15	
	switches					15		1		0.01	1		30	μΑ
	on or all switches					20		5		0.02	5		150	
	off)	HCF				5		1		0.01	1		7.5	
		Types				10		2		0.01	2		15	
						15		4		0.01	4		30	
SWITC	Н				_	V <sub>IS</sub>								
R <sub>ON</sub>	Resistance	нсс	R <sub>L</sub> = 10kΩ•	+ 7.5	- 7.5	+ 7.5 - 7.5 ± 0.25		360 360 775		200 200 280	400 400 850		600 600 1230	
	HCF	HCF				+ 7.5 - 7.5 ± 0.25		370 370 790		200 200 280	400 400 850		520 520 1080	Ω
		нсс	R <sub>L</sub> = 10kΩ•	+ 5	<b>–</b> 5	+ 5 - 5 ± 0.25		600 600 1870		250 250 580	660 660 2000		960 960 2600	_ <b>-</b>
		HCF				+ 5 - 5 ± 0.25		610 610 1900		250 250 580	660 660 2000		840 840 2380	

<sup>\*</sup>  $T_{Low}$ = - 55°C for HCC device : - 40°C for HCF device. \*  $T_{High}$ = + 125°C for HCC device : + 85°C for HCF device.

### STATIC ELECTRICAL CHARACTERISTICS (continued)

			Test	Condi	tions					Value				
Symbol	Parame	ter		V <sub>C</sub> =	Vss	V <sub>DD</sub>	ΤL	.ow*		25°C		T <sub>H</sub>	igh <sup>*</sup>	Unit
Cymbol	- urumo			V <sub>DD</sub>	(V)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
SWITC	H (continued	)												
R <sub>ON</sub> Resistance	нсс	R <sub>L</sub> = 10kΩ•	+ 15	0	+ 15 + 0.25 + 9.3		360 360 775		200 200 300	400 400 850		600 600 1230		
		HCF	_	+ 15	0	+ 15 + 0.25 + 9.3		370 370 790		200 200 300	400 400 800		520 520 1080	$\Omega$
	HCC HCF	нсс	R <sub>L</sub> = 10kΩ•	+ 10	0	+ 10 + 0.25 + 5.6		600 600 1870		250 250 560	660 660 2000		960 960 2600	
		HCF		+ 10	0	+ 10 + 0.25 + 5.6		610 610 1900		250 250 560	660 660 2000		840 840 2380	
ΔΟΝ	ΔΟΝ Resistance ΔRON (between any 2 of 4 switches)		R <sub>L</sub> = 10kΩ•	+ 7.5	- 7.5	± 7.5				10				Ω
				+ 5	- 5	± 5				15				. 32
Input or Leakage Switch C	Current	нсс		V <sub>DD</sub> +18	V <sub>C</sub> = V <sub>SS</sub>			± 0.1		10 <sup>-5</sup>	± 0.1		1	
(effective resistance		HCF		V <sub>DD</sub> + 15	V <sub>C</sub> = V <sub>SS</sub>			± 0.3		10 <sup>-5</sup>	± 0.3		1	μΑ
Cı	Input Capad	citance			•					4				
Co	Output Capacitance	9	V <sub>CC</sub> = V <sub>SS</sub> =	= - 5		+ 5				4				pF
C <sub>IO</sub>	Feedthroug									0.2				
	ROL (V <sub>C</sub> )							<u> </u>		·	·			<u> </u>
$V_{TH}$	Switch Thre	shold				5	1		1	2.25		1		
	Voltage		$I_{IS} = 10\mu A$			10	2		2	4.5		2		V
						15	2		2	6.75		2		
l <sub>1</sub>	Input Current	HCC Types	$V_{IS} \leq V_{DD}$			18		± 0.1		±10 <sup>-5</sup>	± 0.1		± 1	μA
		HCF Types				15		± 0.3		±10 <sup>-5</sup>	± 0.3		± 1	
Cı	Input Capad	citance								5	7.5			pF



<sup>\*</sup>  $T_{Low}$ = - 55°C for HCC device : - 40°C for HCF device. \*  $T_{High}$ = + 125°C for HCC device : + 85°C for HCF device.

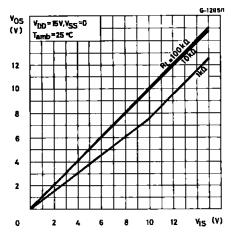
**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}C$ ,  $C_{L} = 50 pF$  all input square wave rise and fall time = 20ns)

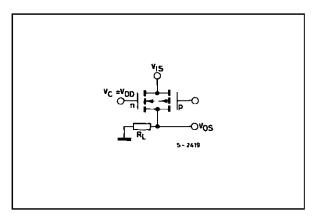
			Test	Condi	tions			Va	lue	
Parameter	<b>V</b> <sub>C</sub> (V)	<b>R</b> <sub>L</sub> (kΩ)	f <sub>i</sub> (KHz)	V <sub>1</sub> (V)	V <sub>ss</sub> (V)	<b>V</b> <sub>DD</sub> (V)		Тур.	Max.	Unit
SWITCH	•					•		•	•	•
t <sub>pd</sub> Propagation Delay Time (signal intput to output)	_ V	10		10sq.	GND	5 10		40 20	100	
(0.3	= V <sub>DD</sub>	10		Wave	GIND	15		15	50 40	ns
Crosstalk Between any 2 of 4 Switches (f @ - 50dB) 20 log 10 $\frac{V_{O(B)}}{V_{I(A)}} = -50dB$	$V_{C(A)} = V_{DD} = +5$ $V_{C(B)} = V_{SS} = -5$	1		V <sub>I(A)</sub> Δ = 5p-p				0.9		MHz
Frequency Response Switch "ON" (sine wave input) At 20 log 10 $\frac{V_0}{V_1} = -3 dB$	= V <sub>DD</sub> = + 5	1		5р-р	- 5			40		MHz
Feedtrough (switch OFF) At 20 log 10 $\frac{V_0}{V_1} = -50 \text{dB}$	= V <sub>SS</sub> = - 5	1		– 5р-р		5		1.25		MHz
Sine Wave Distortion	= V <sub>DD</sub> = 5	10	1	5р-р	- 5			0.4		%
CONTROL (V <sub>C</sub> )										
Propagation Delay : (turn on control to output)	V <sub>DD</sub> - V <sub>SS</sub> (sq. wawe)	1		V <sub>DD</sub> or V <sub>SS</sub>		5 10 15	V <sub>DD</sub> -V <sub>SS</sub> = 10V	35 20 15	70 40 30	ns
Max. Allowable Control Input Repetition Rate	10 (sq. wawe)	1		V <sub>DD</sub>	GND	10		10	30	MHz
Crosstalk (control input to signal output)	10 (sq. wave)	10			GND	10		50		mV

 $(\Delta)$  Symmetrical about OV

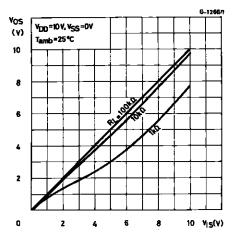
(ullet) For all test conditions.

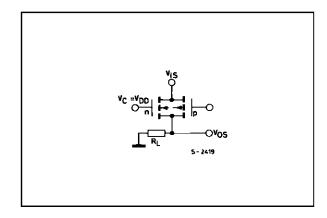
Typical "ON" Characteristics for 1 of 4 switches with  $V_{DD} = +15V$ ,  $V_{SS} = 0V$ , and Test Circuit.



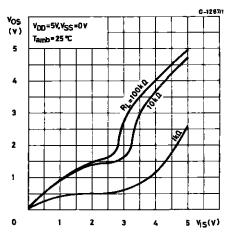


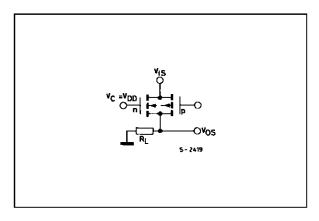
Typical "ON" Characteristics for 1 of 4 switches with  $V_{DD} = + 10V$ ,  $V_{SS} = 0V$ , and Test Circuit.



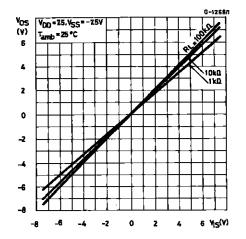


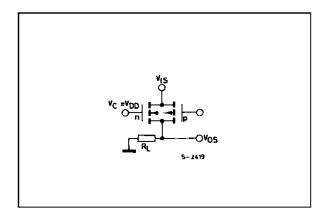
Typical "ON" Characteristics for 1 of 4 switches with  $V_{DD} = +5V$ ,  $V_{SS} = 0V$ , and Test Circuit.

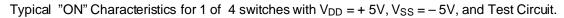


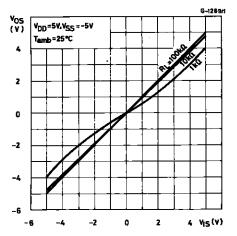


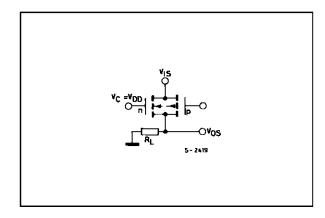
Typical "ON" Characteristics for 1 of 4 switches with  $V_{DD} = +7.5V$ ,  $V_{SS} = -7.5V$ , and Test Circuit.



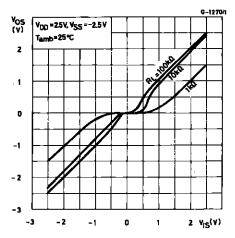


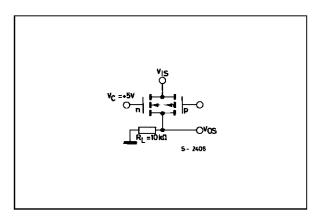




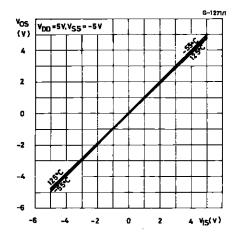


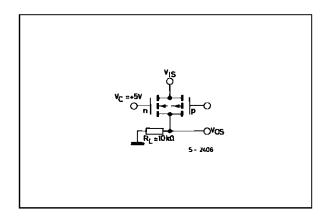
Typical "ON" Characteristics for 1 of 4 switches with  $V_{DD} = +2.5V$ ,  $V_{SS} = -2.5V$ , and Test Circuit.



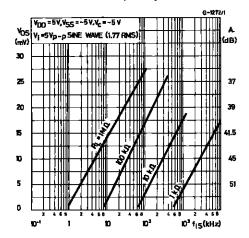


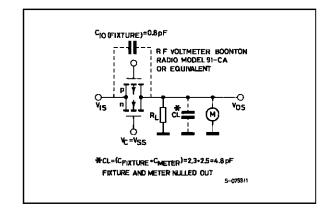
Typical "ON" Characteristics as function of temp.for 1 of 4 switches with  $V_{DD} = + 5V$  and Test Circuit.



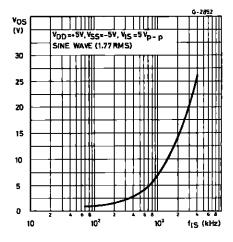


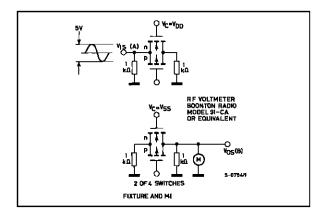
Typical feedthru vs. frequency-switch "OFF" and Test Circuit.



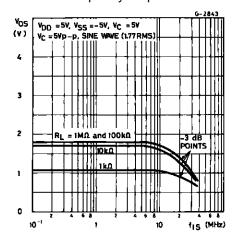


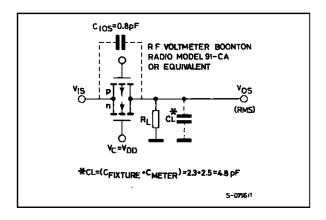
Typical Crosstalk between Switch Circuits in the Same Package.





Typical Switch Frequency response-switch "ON" and Test Circuit.





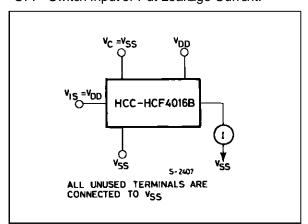
TYPICAL "ON" RESISTANCE CHARACTERISTICS,  $T_{amb} = 25^{\circ}C$ 

	Sup	ply			Load Co	nditions			
Characteristic*	Cond	itions	R <sub>L</sub> =	<b>1 k</b> Ω	R <sub>L</sub> =	<b>10 k</b> Ω	$R_L = 100 \text{ k}\Omega$		
	<b>V</b> <sub>DD</sub> (V)	V <sub>ss</sub> (V)	Value (Ω)	V <sub>is</sub> (V)	Value (Ω)	V <sub>is</sub> (V)	Value (Ω)	V <sub>is</sub> (V)	
R <sub>ON</sub>	+ 15	0	200	+ 15	200	+ 15	180	+ 15	
KON		U	200	0	200	0	200	0	
R <sub>ON</sub> (max)	+ 15	0	300	+ 11	300	+ 9.3	320	+ 9.2	
6	+ 10	0	290	+ 10	250	+ 10	240	+ 10	
Ron			290	0	250	0	300	0	
R <sub>ON</sub> (max)	+ 10	0	500	+ 7.4	560	+ 5.6	610	+5.5	
Ron	+ 5	0	860	+ 5	470	+ 5	450	+ 5	
KON	+ 5	U	600	0	580	0	800	0	
R <sub>ON</sub> (max)	+ 5	0	1.7k	+ 4.2	7k	+ 2.9	33k	+2.7	
D.	+ 2.5	- 2.5	590	+ 2.5	450	+ 2.5	490	+ 2.5	
R <sub>ON</sub>	T 2.0	- 2.5	720	- 2.5	520	- 2.5	520	- 2.5	
R <sub>ON</sub> (max)	+ 2.5	- 2.5	232k	± 0.25	300k	± 0.25	870k	± 0.25	

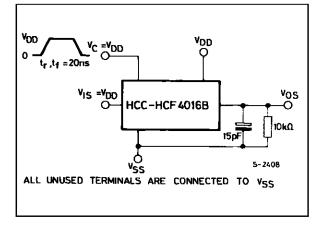
<sup>\*</sup> Variation from a perfect switch,  $R_{ON} = 0\Omega$ .

### **TEST CIRCUITS**

"OFF" Switch Input or Put Leakage Current.

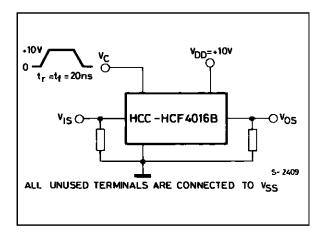


### Square-Wave Response.

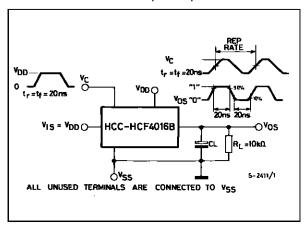


#### **TEST CIRCUITS** (continued)

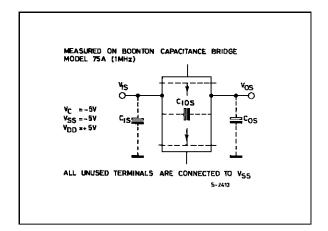
Crosstalk-control Input to Signal Output.



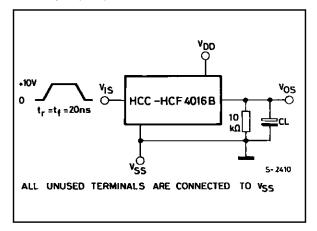
Max Allowable Control-input Repetition Rate.



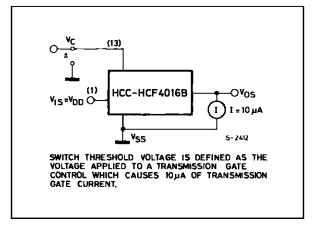
Capacitance C<sub>IOS</sub> and C<sub>OS</sub>.



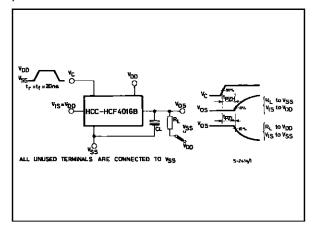
Propagaton Delay Time Signal Input  $(V_{IS})$  to Signal Output  $(V_{OS})$ .



Switch Treshold Voltage.

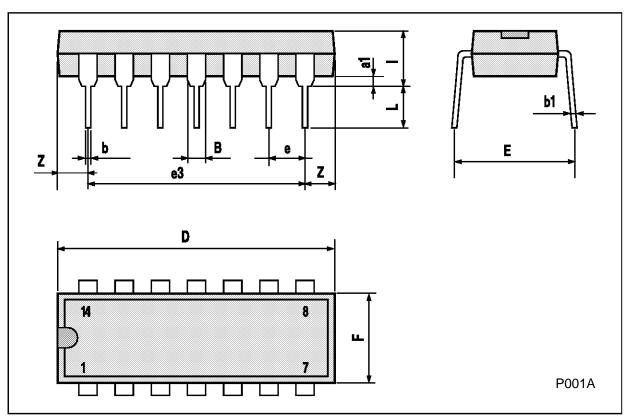


Turn-On Propagation Delay-control Input to Output.



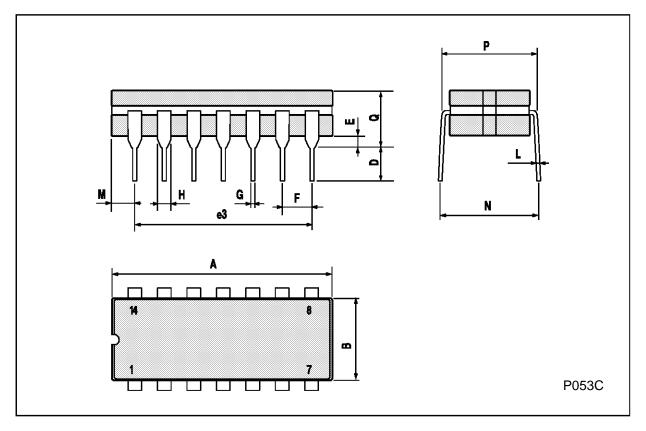
# Plastic DIP14 MECHANICAL DATA

DIM.		mm				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



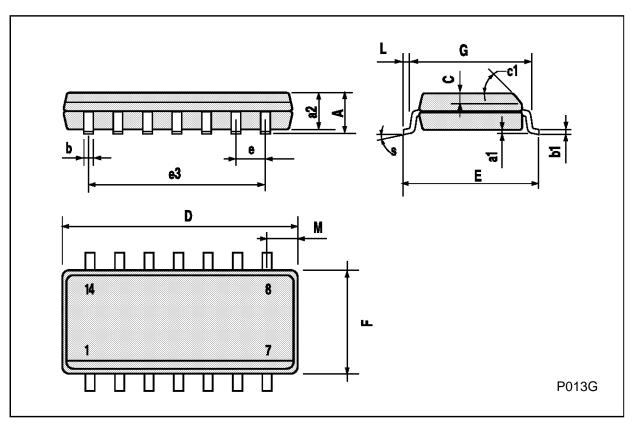
# **Ceramic DIP14/1 MECHANICAL DATA**

DIM.		mm		inch				
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			20			0.787		
В			7.0			0.276		
D		3.3			0.130			
E	0.38			0.015				
e3		15.24			0.600			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
M	1.52		2.54	0.060		0.100		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



# **SO14 MECHANICAL DATA**

DIM.		mm			inch		
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45°	(typ.)			
D	8.55		8.75	0.336		0.344	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		7.62			0.300		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.68			0.026	
S			8° (ı	max.)			



## PLCC20 MECHANICAL DATA

DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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